

C1
Cont
19. The device of claim 18, wherein the semiconductor element is a laser diode having a laser light-emitting semiconductor multilayer formed on the major face of the substrate, wherein the side cleavage plane of the sapphire substrate is connected with a side cleavage plane of the multilayer.

20. A sapphire monocrystal plate having a major face and a working reference plane on a peripheral edge of the plate, the working reference plane being substantially parallel or perpendicular to a plane R of the sapphire monocrystal, the working reference plane being used as a mark to form on the major surface a microcrack line parallel to the plane R for starting to cleave the plate.

21. The sapphire monocrystal plate of claim 20, wherein an angle between the working reference plane and the plane R is between about -10 to +10 degrees or about 80 to 100 degrees.--

REMARKS:

Minor changes have been made to the specification. Claims 1-8 are canceled without prejudice. Claims 9-16 have been canceled. New claims 17-21 are added. Claims 17-21 are pending. Reconsideration and reexamination of the application, as amended, is respectfully requested.

Claims 1-8 were rejected under 35 U.S.C. §112, second paragraph as being indefinite. This rejection is moot in view of the cancellation of the claims. Claims 2-8 are re-written as claims 17-21 to overcome the §112, second paragraph rejections.

Claims 1 was rejected as being "anticipated by the applicant's own admission." This rejection is moot in view of the cancellation of claim 1.

Claims 1-4 and 6-8 were rejected as being anticipated by Setsune (JP 61-121042). This rejection, to the extent applicable to the new claims 17-21, is respectfully traversed.

Setsune described an optical waveguide formed on a sapphire substrate where the input-side and output-side end faces are produced by cleavage along the R surface of the sapphire.